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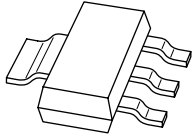
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Kind regards,

Team Nexperia



# PBSS304NZ

60 V, 5.2 A NPN low  $V_{CEsat}$  (BISS) transistor

Rev. 02 — 20 November 2009

Product data sheet

## 1. Product profile

### 1.1 General description

NPN low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) small Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS304PZ.

### 1.2 Features

- Low collector-emitter saturation voltage  $V_{CEsat}$
- High collector current capability  $I_C$  and  $I_{CM}$
- High collector current gain ( $h_{FE}$ ) at high  $I_C$
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

### 1.3 Applications

- High-voltage DC-to-DC conversion
- High-voltage MOSFET gate driving
- High-voltage motor control
- High-voltage power switches (e.g. motors, fans)
- Automotive applications

### 1.4 Quick reference data

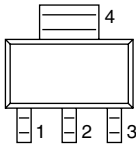
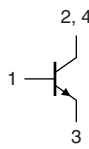
Table 1. Quick reference data

| Symbol      | Parameter                               | Conditions                       | Min                   | Typ | Max  | Unit       |
|-------------|---|----------------------------------|-----------------------|-----|------|------------|
| $V_{CEO}$   | collector-emitter voltage               | open base                        | -                     | -   | 60   | V          |
| $I_C$       | collector current                       |                                  | -                     | -   | 5.2  | A          |
| $I_{CM}$    | peak collector current                  | single pulse;<br>$t_p \leq 1$ ms | -                     | -   | 10.4 | A          |
| $R_{CEsat}$ | collector-emitter saturation resistance | $I_C = 4$ A;<br>$I_B = 200$ mA   | <a href="#">[1]</a> - | 39  | 55   | m $\Omega$ |

[1] Pulse test:  $t_p \leq 300$   $\mu$ s;  $\delta \leq 0.02$ .

## 2. Pinning information

Table 2. Pinning

| Pin | Description | Simplified outline  | Symbol  |
|-----|-------------|---|---|
| 1   | base        |  |  |
| 2   | collector   |   |   |
| 3   | emitter     |   |   |
| 4   | collector   |   |   |

## 3. Ordering information

Table 3. Ordering information

| Type number | Package |   |         |
|-------------|---------|---|---------|
|             | Name    | Description   | Version |
| PBSS304NZ   | SC-73   | plastic surface-mounted package with increased heatsink;<br>4 leads | SOT223  |

## 4. Marking

Table 4. Marking codes

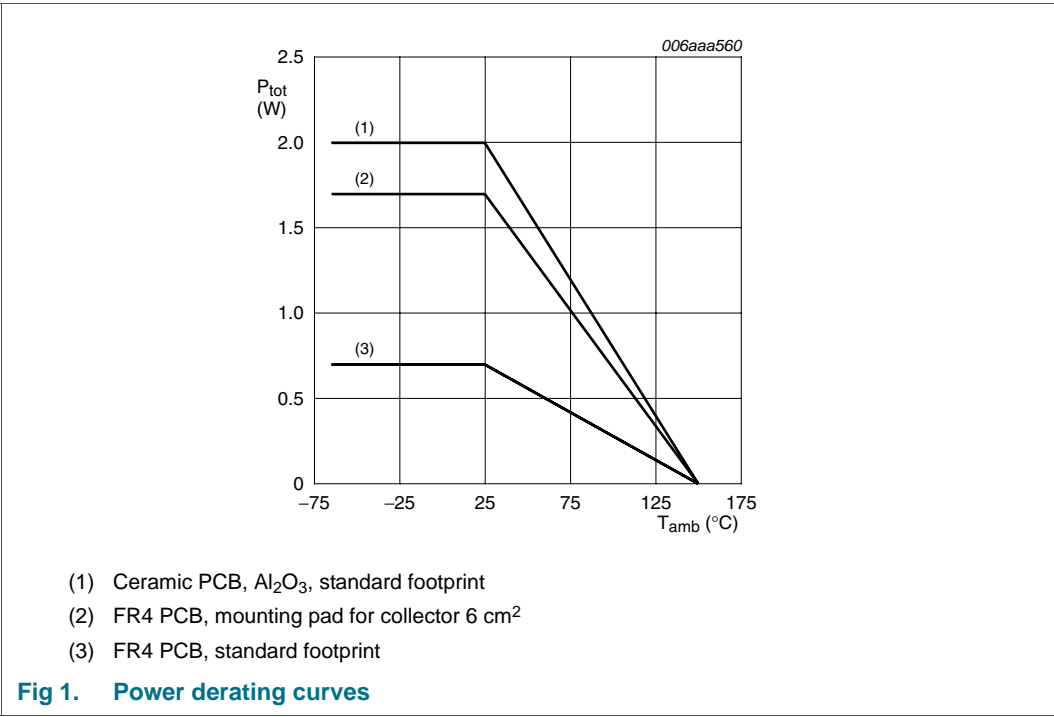
| Type number | Marking code |
|-------------|--------------|
| PBSS304NZ   | S304NZ       |

5. Limiting values

**Table 5. Limiting values**  
*In accordance with the Absolute Maximum Rating System (IEC 60134).*

| Symbol    | Parameter                 | Conditions                                | Min   | Max  | Unit               |
|-----------|---------------------------|---|-------|------|--------------------|
| $V_{CBO}$ | collector-base voltage    | open emitter                              | -     | 60   | V                  |
| $V_{CEO}$ | collector-emitter voltage | open base                                 | -     | 60   | V                  |
| $V_{EBO}$ | emitter-base voltage      | open collector                            | -     | 5    | V                  |
| $I_C$     | collector current         |   | -     | 5.2  | A                  |
| $I_{CM}$  | peak collector current    | single pulse;<br>$t_p \leq 1\text{ ms}$   | -     | 10.4 | A                  |
| $P_{tot}$ | total power dissipation   | $T_{amb} \leq 25\text{ }^{\circ}\text{C}$ | [1] - | 0.7  | W                  |
|           |                           |   | [2] - | 1.7  | W                  |
|           |                           |   | [3] - | 2.0  | W                  |
| $T_j$     | junction temperature      |   | -     | 150  | $^{\circ}\text{C}$ |
| $T_{amb}$ | ambient temperature       |   | -65   | +150 | $^{\circ}\text{C}$ |
| $T_{stg}$ | storage temperature       |   | -65   | +150 | $^{\circ}\text{C}$ |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.  
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.  
[3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

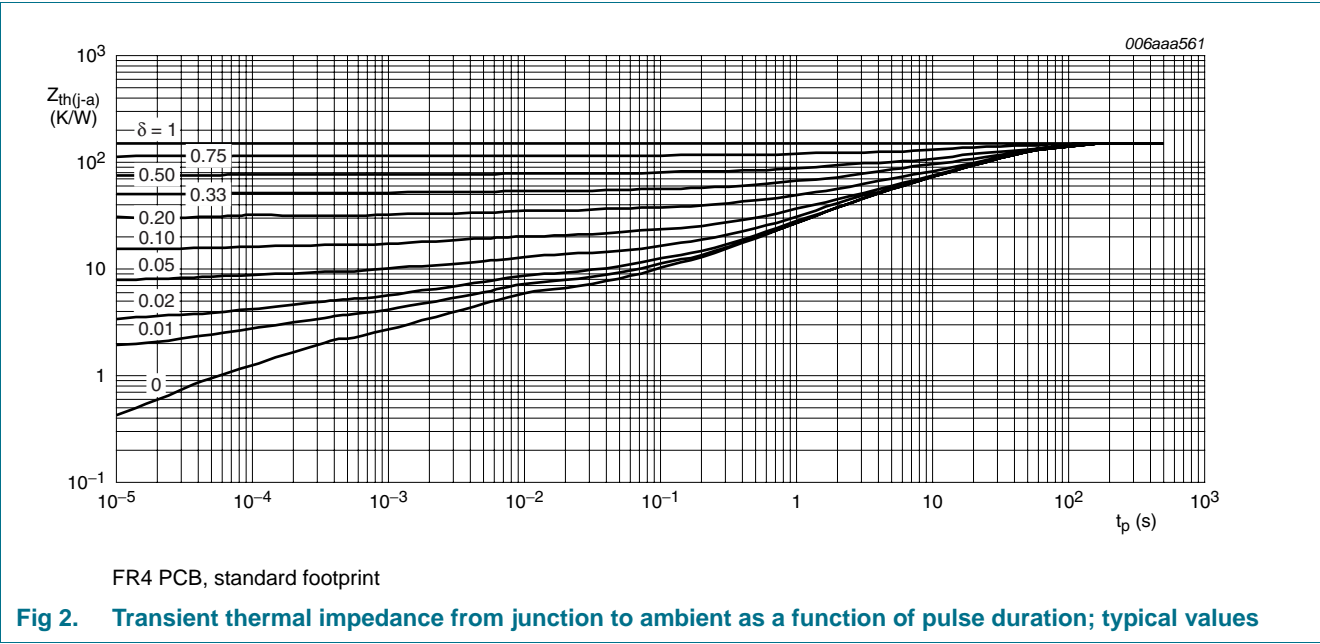


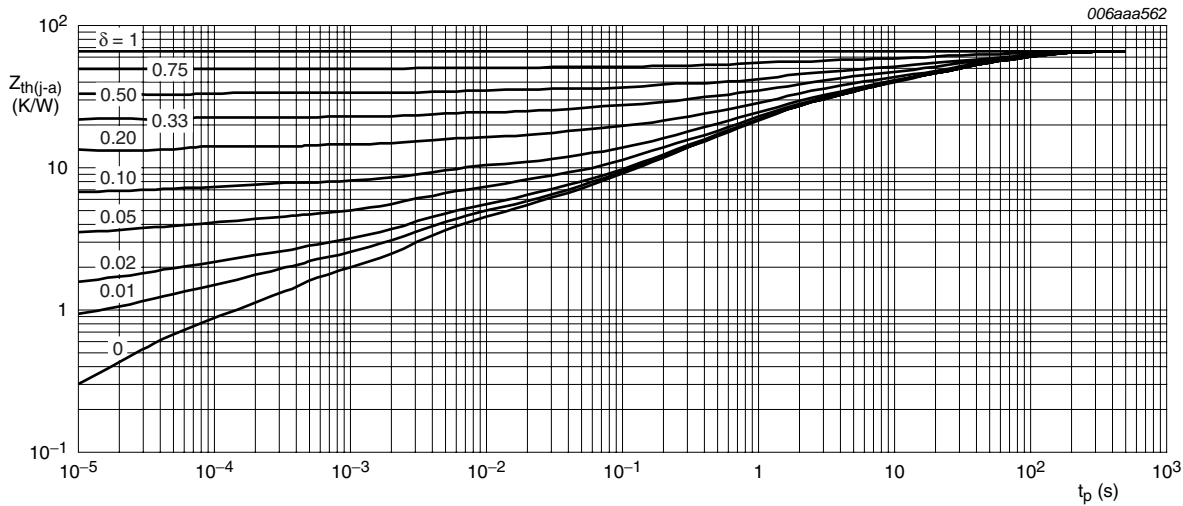
6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter  | Conditions  | Min   | Typ | Max | Unit |
|----------------|--|-------------|-------|-----|-----|------|
| $R_{th(j-a)}$  | thermal resistance from junction to ambient      | in free air | [1] - | -   | 179 | K/W  |
|                |  |             | [2] - | -   | 74  | K/W  |
|                |  |             | [3] - | -   | 63  | K/W  |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point |             | -     | -   | 15  | K/W  |

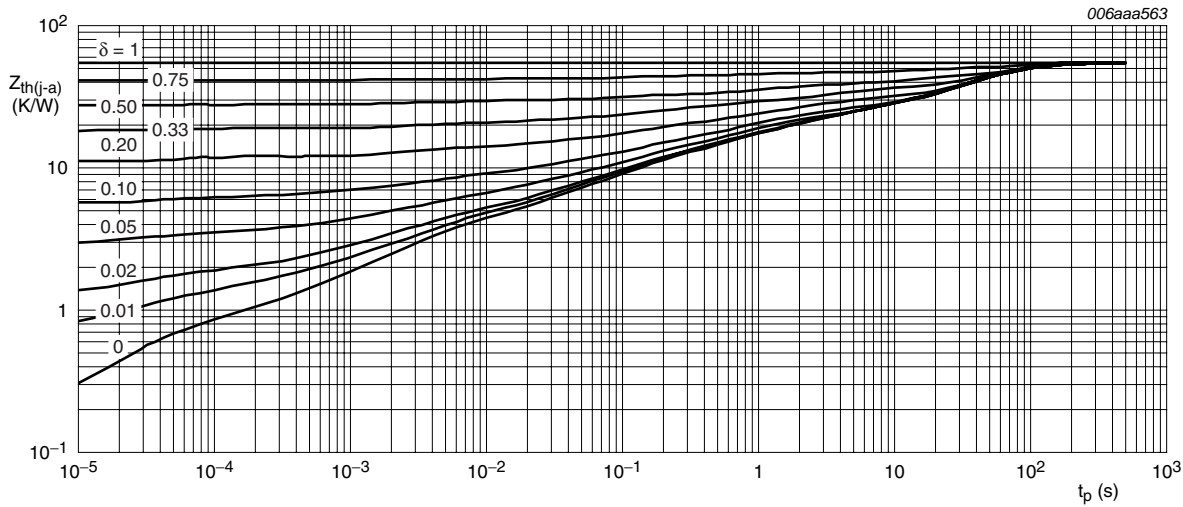
- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.  
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.  
[3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.





FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

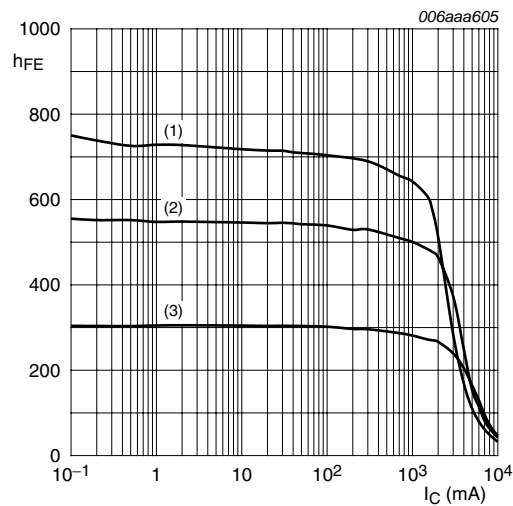
## 7. Characteristics

**Table 7. Characteristics**

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

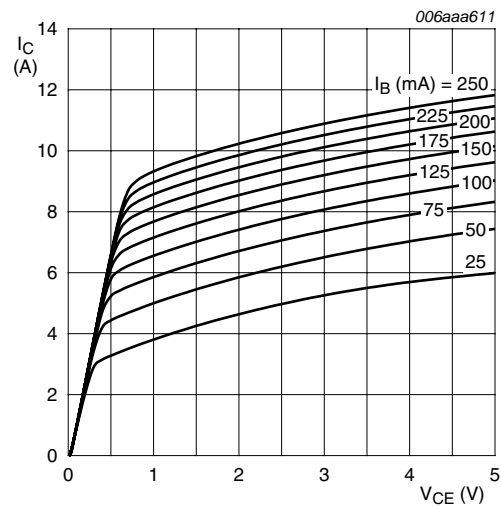
| Symbol      | Parameter                               | Conditions   | Min | Typ | Max  | Unit                |
|-------------|---|--|-----|-----|------|---------------------|
| $I_{CBO}$   | collector-base cut-off current          | $V_{CB} = 60\text{ V}; I_E = 0\text{ A}$   | -   | -   | 100  | nA                  |
|             |   | $V_{CB} = 60\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$                    | -   | -   | 50   | $\mu\text{A}$       |
| $I_{EBO}$   | emitter-base cut-off current            | $V_{EB} = 5\text{ V}; I_C = 0\text{ A}$  | -   | -   | 100  | nA                  |
| $h_{FE}$    | DC current gain                         | $V_{CE} = 2\text{ V}; I_C = 0.5\text{ A}$  | [1] | 300 | 520  | -                   |
|             |   | $V_{CE} = 2\text{ V}; I_C = 1\text{ A}$  | [1] | 300 | 500  | -                   |
|             |   | $V_{CE} = 2\text{ V}; I_C = 2\text{ A}$  | [1] | 250 | 470  | -                   |
|             |   | $V_{CE} = 2\text{ V}; I_C = 4\text{ A}$  | [1] | 150 | 250  | -                   |
|             |   | $V_{CE} = 2\text{ V}; I_C = 6\text{ A}$  | [1] | 80  | 120  | -                   |
| $V_{CEsat}$ | collector-emitter saturation voltage    | $I_C = 0.5\text{ A}; I_B = 50\text{ mA}$   | [1] | -   | 25   | 35 mV               |
|             |   | $I_C = 1\text{ A}; I_B = 50\text{ mA}$   | [1] | -   | 50   | 70 mV               |
|             |   | $I_C = 1\text{ A}; I_B = 10\text{ mA}$   | [1] | -   | 85   | 120 mV              |
|             |   | $I_C = 2\text{ A}; I_B = 40\text{ mA}$   | [1] | -   | 105  | 150 mV              |
|             |   | $I_C = 4\text{ A}; I_B = 200\text{ mA}$  | [1] | -   | 155  | 220 mV              |
|             |   | $I_C = 4\text{ A}; I_B = 400\text{ mA}$  | [1] | -   | 145  | 210 mV              |
|             |   | $I_C = 4\text{ A}; I_B = 80\text{ mA}$   | [1] | -   | 205  | 305 mV              |
|             |   | $I_C = 5.2\text{ A}; I_B = 260\text{ mA}$  | [1] | -   | 200  | 280 mV              |
| $R_{CEsat}$ | collector-emitter saturation resistance | $I_C = 4\text{ A}; I_B = 200\text{ mA}$  | [1] | -   | 39   | 55 $\text{m}\Omega$ |
|             |   | $I_C = 4\text{ A}; I_B = 80\text{ mA}$   | [1] | -   | 51   | 76 $\text{m}\Omega$ |
| $V_{BEsat}$ | base-emitter saturation voltage         | $I_C = 1\text{ A}; I_B = 100\text{ mA}$  | [1] | -   | 0.82 | 0.9 V               |
|             |   | $I_C = 4\text{ A}; I_B = 400\text{ mA}$  | [1] | -   | 0.94 | 1.05 V              |
| $V_{BEon}$  | base-emitter turn-on voltage            | $V_{CE} = 2\text{ V}; I_C = 2\text{ A}$  | [1] | -   | 0.75 | 0.85 V              |
| $t_d$       | delay time                              | $V_{CC} = 12.5\text{ V}; I_C = 3\text{ A}; I_{Bon} = 0.15\text{ A}; I_{Boff} = -0.15\text{ A}$ | -   | 15  | -    | ns                  |
| $t_r$       | rise time                               |  | -   | 95  | -    | ns                  |
| $t_{on}$    | turn-on time                            |  | -   | 110 | -    | ns                  |
| $t_s$       | storage time                            |  | -   | 360 | -    | ns                  |
| $t_f$       | fall time                               |  | -   | 195 | -    | ns                  |
| $t_{off}$   | turn-off time                           |  | -   | 555 | -    | ns                  |
| $f_T$       | transition frequency                    | $V_{CE} = 10\text{ V}; I_C = 100\text{ mA}; f = 100\text{ MHz}$                                | -   | 130 | -    | MHz                 |
| $C_c$       | collector capacitance                   | $V_{CB} = 10\text{ V}; I_E = I_C = 0\text{ A}; f = 1\text{ MHz}$                               | -   | 48  | 70   | pF                  |

[1] Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$ .



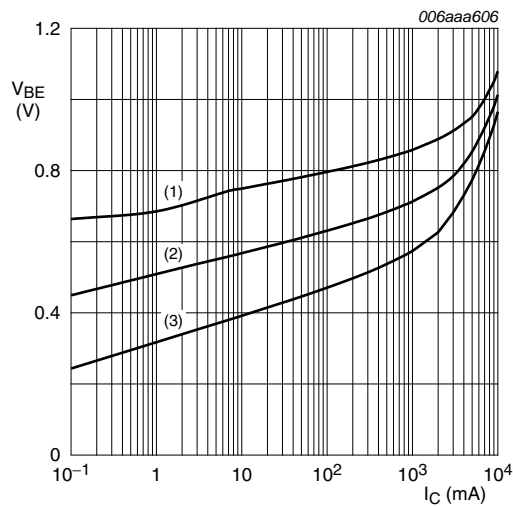
- $V_{CE} = 2\text{ V}$
- (1)  $T_{amb} = 100\text{ }^{\circ}\text{C}$
  - (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$
  - (3)  $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 5. DC current gain as a function of collector current; typical values



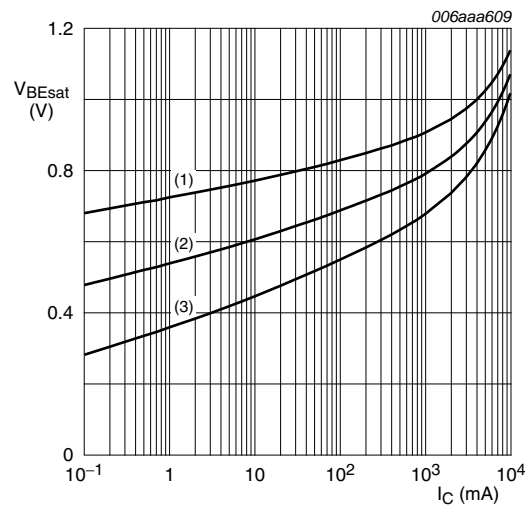
$T_{amb} = 25\text{ }^{\circ}\text{C}$

Fig 6. Collector current as a function of collector-emitter voltage; typical values



- $V_{CE} = 2\text{ V}$
- (1)  $T_{amb} = -55\text{ }^{\circ}\text{C}$
  - (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$
  - (3)  $T_{amb} = 100\text{ }^{\circ}\text{C}$

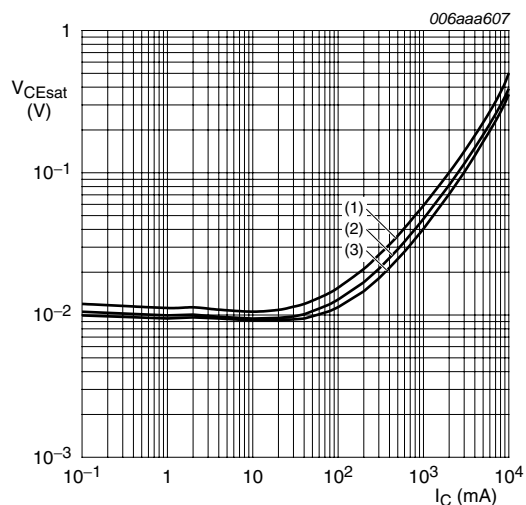
Fig 7. Base-emitter voltage as a function of collector current; typical values



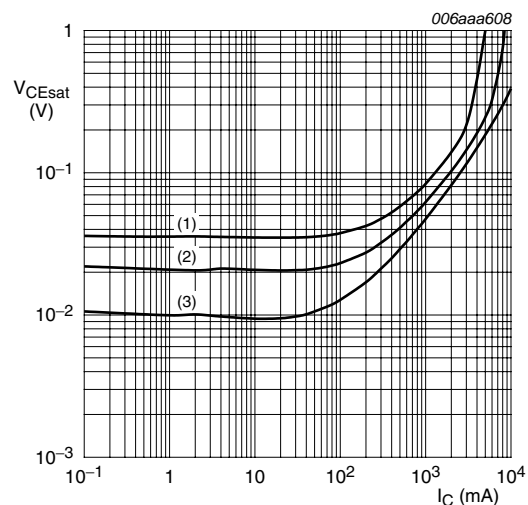
- $I_C/I_B = 20$
- (1)  $T_{amb} = -55\text{ }^{\circ}\text{C}$
  - (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$
  - (3)  $T_{amb} = 100\text{ }^{\circ}\text{C}$

Fig 8. Base-emitter saturation voltage as a function of collector current; typical values

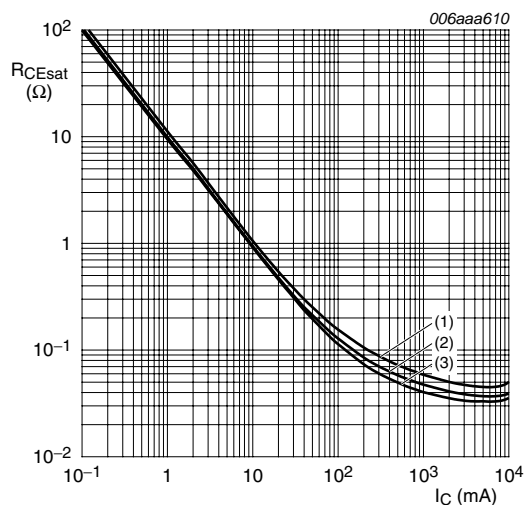




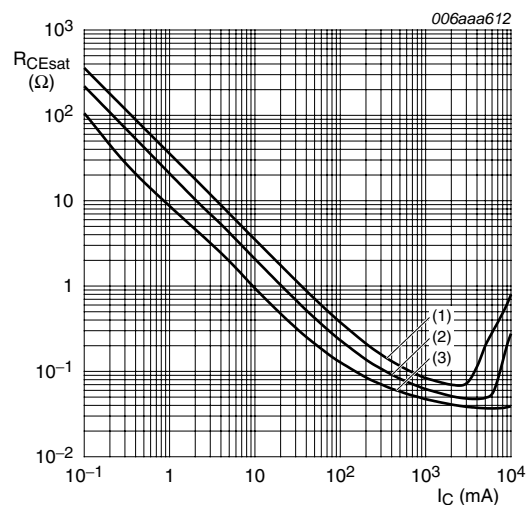
**Fig 9.** Collector-emitter saturation voltage as a function of collector current; typical values



**Fig 10.** Collector-emitter saturation voltage as a function of collector current; typical values



**Fig 11.** Collector-emitter saturation resistance as a function of collector current; typical values



**Fig 12.** Collector-emitter saturation resistance as a function of collector current; typical values

8. Test information

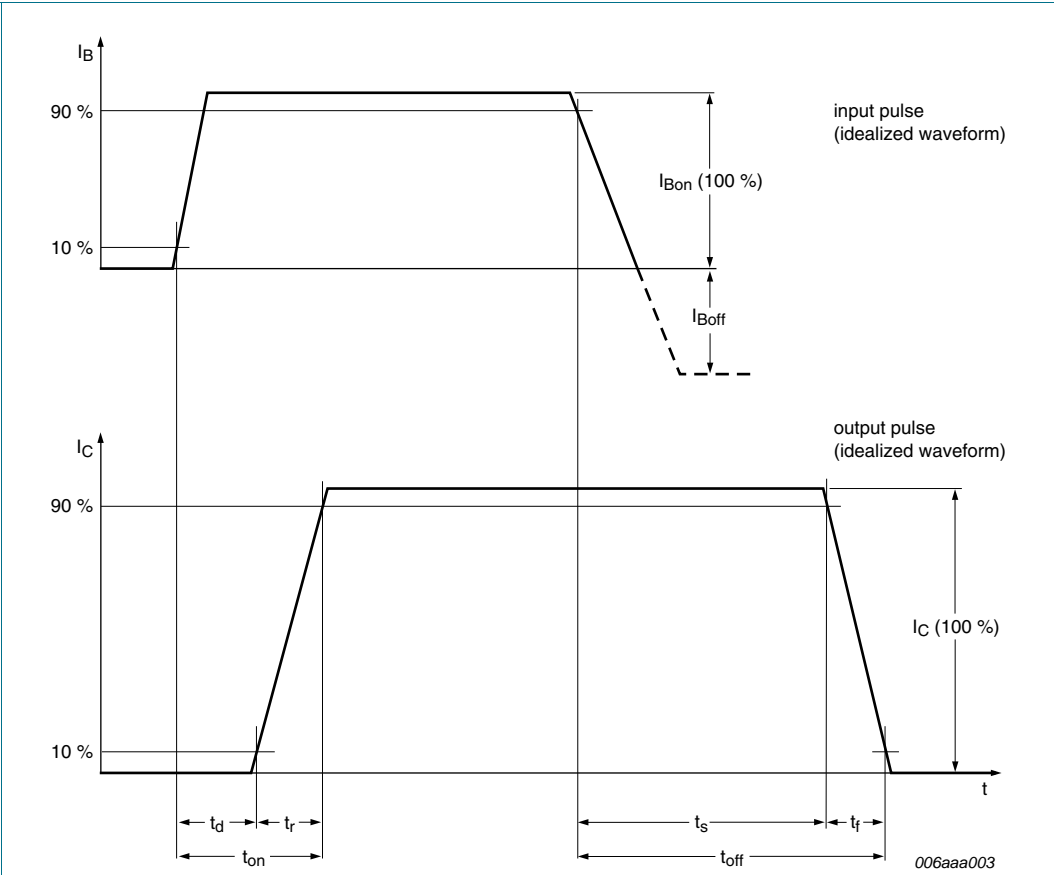


Fig 13. BISS transistor switching time definition

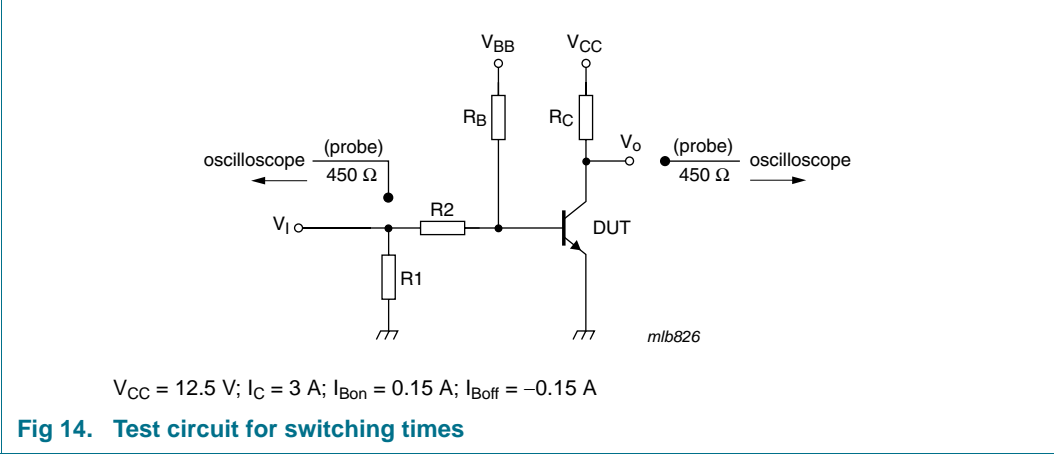
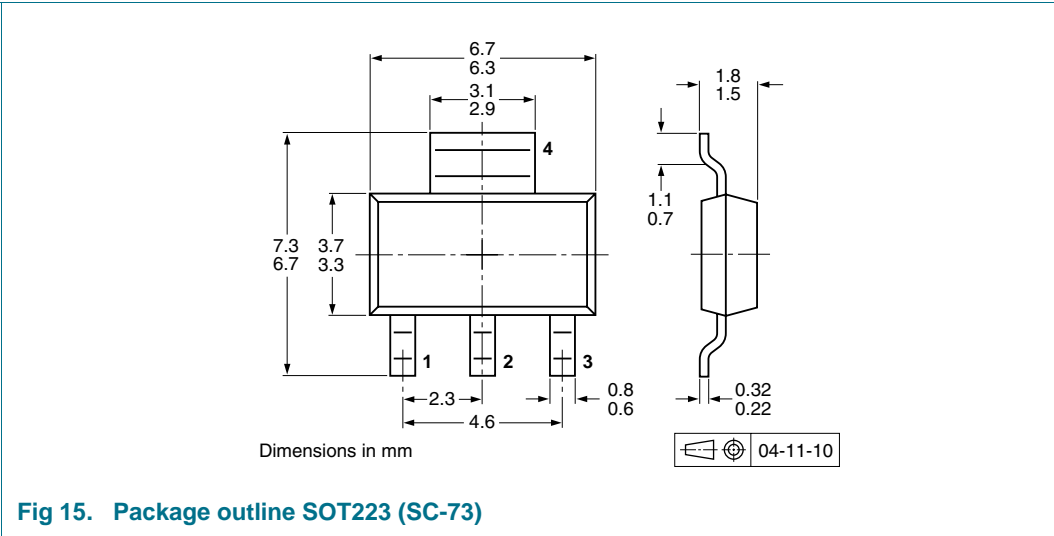


Fig 14. Test circuit for switching times

9. Package outline



10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.<sup>[1]</sup>

| Type number | Package | Description                     | Packing quantity |      |
|-------------|---------|---------------------------------|------------------|------|
|             |         |                                 | 1000             | 4000 |
| PBSS304NZ   | SOT223  | 8 mm pitch, 12 mm tape and reel | -115             | -135 |

[1] For further information and the availability of packing methods, see [Section 14](#).

11. Soldering

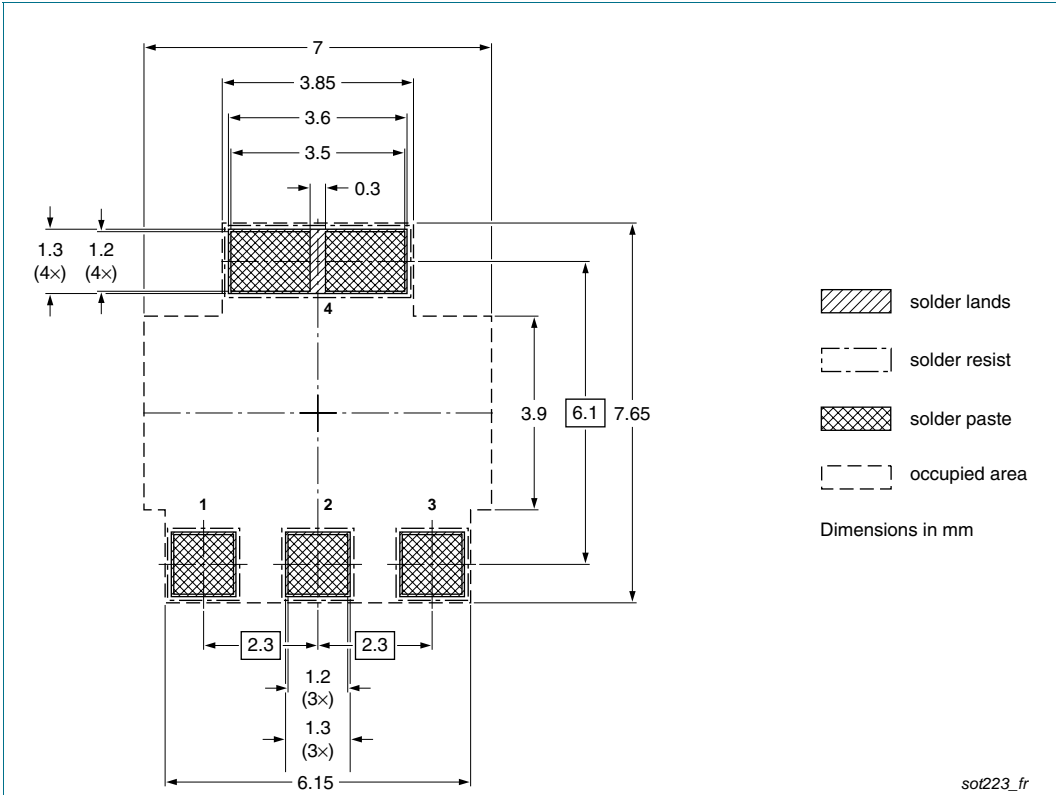


Fig 16. Reflow soldering footprint

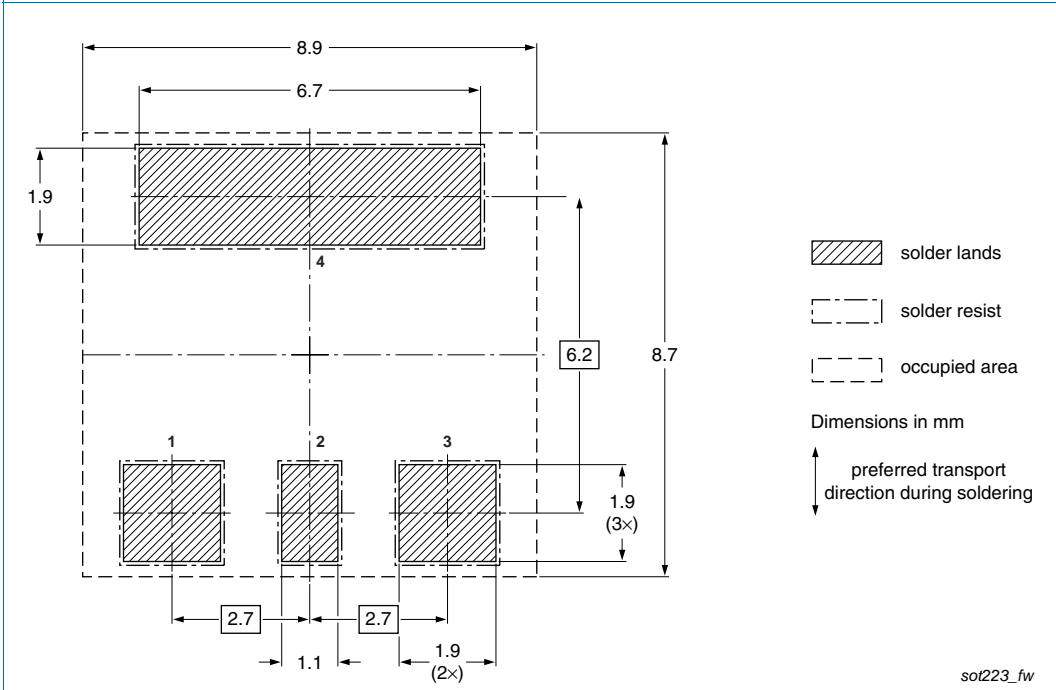


Fig 17. Wave soldering footprint

## 12. Revision history

Table 9. Revision history

| Document ID    | Release date  | Data sheet status  | Change notice | Supersedes  |
|----------------|---|--------------------|---------------|-------------|
| PBSS304NZ_2    | 20091120  | Product data sheet | -             | PBSS304NZ_1 |
| Modifications: | <ul style="list-style-type: none"><li>• This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.</li><li>• <a href="#">Figure 16 "Reflow soldering footprint"</a>: updated</li><li>• <a href="#">Figure 17 "Wave soldering footprint"</a>: updated</li></ul> |                    |               |             |
| PBSS304NZ_1    | 20060918  | Product data sheet | -             | -           |

## 13. Legal information

### 13.1 Data sheet status

| Document status <sup>[1][2]</sup> | Product status <sup>[3]</sup> | Definition  |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet      | Development                   | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet    | Qualification                 | This document contains data from the preliminary specification.                       |
| Product [short] data sheet        | Production                    | This document contains the product specification.                                     |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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